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FAIRCHILD SEMICONDUCTOR®

March 2008

FDMC8462

N-Channel Power Trench® MOSFET

40V, 20A, 5.8mΩ

Features

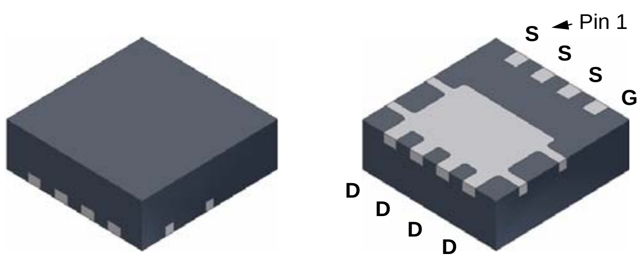
- Max $r_{DS(on)}$ = 5.8mΩ at V_{GS} = 10V, I_D = 13.5A
- Max $r_{DS(on)}$ = 8.0mΩ at V_{GS} = 4.5V, I_D = 11.8A
- Low Profile - 1mm max in Power 33
- 100% UIL Tested
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

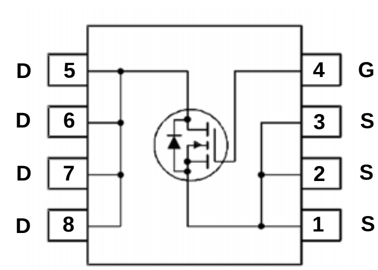
- DC - DC Conversion



Top

Bottom

Power 33



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) T_C = 25°C	20	A
	-Continuous (Silicon limited) T_C = 25°C	64	
	-Continuous T_A = 25°C (Note 1a)	14	
	-Pulsed	50	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	216	mJ
P_D	Power Dissipation T_C = 25°C	41	W
	Power Dissipation T_A = 25°C (Note 1a)	2.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8462	FDMC8462	Power 33	13''	12mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		31		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 32V,			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-6.6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 13.5A		4.7	5.8	mΩ
		V_{GS} = 4.5V, I_D = 11.8A		6.4	8.0	
		V_{GS} = 10V, I_D = 13.5A, T_J = 125°C		7.1	9.3	
g_{FS}	Forward Transconductance	V_{DD} = 5V, I_D = 13.5A		60		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz		2000	2660	pF
C_{oss}	Output Capacitance			545	725	pF
C_{rss}	Reverse Transfer Capacitance			80	120	pF
R_g	Gate Resistance	f = 1MHz		2.7		Ω

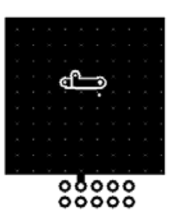
Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 20V, I_D = 13.5A, V_{GS} = 10V, R_{GEN} = 6Ω		12	21	ns
t_r	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	43	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	V_{GS} = 0V to 10V; V_{DD} = 20V, I_D = 13.5A		30	43	nC
Q_g	Total Gate Charge	V_{GS} = 0V to 4.5V		15	21	nC
Q_{gs}	Gate to Source Charge			6		nC
Q_{gd}	Gate to Drain “Miller” Charge			5		nC

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 13.5A (Note 2)		0.8	1.3	V
		V_{GS} = 0V, I_S = 1.7A (Note 2)		0.7	1.2	
t_{rr}	Reverse Recovery Time	I_F = 13.5A, di/dt = 100A/μs		35	57	ns
Q_{rr}	Reverse Recovery Charge			20	32	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53°C/W when mounted on a 1 in^2 pad of 2 oz copper

b. 125°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.
3. Starting T_J = 25°C; N-ch: L = 3 mH, I_{AS} = 12A, V_{DD} = 40V, V_{GS} = 10V

Typical Characteristics T_J = 25°C unless otherwise noted

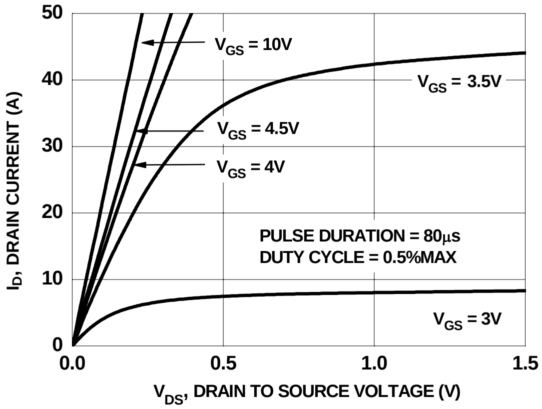


Figure 1. On-Region Characteristics

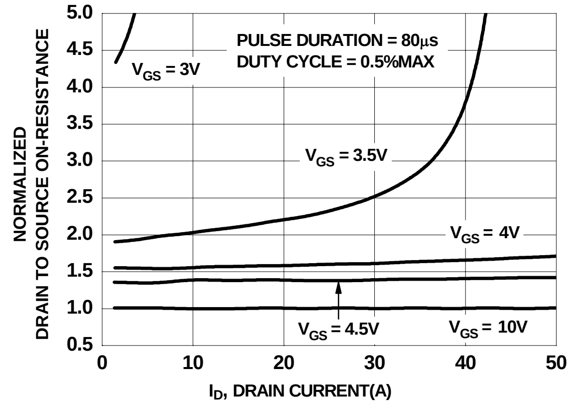


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

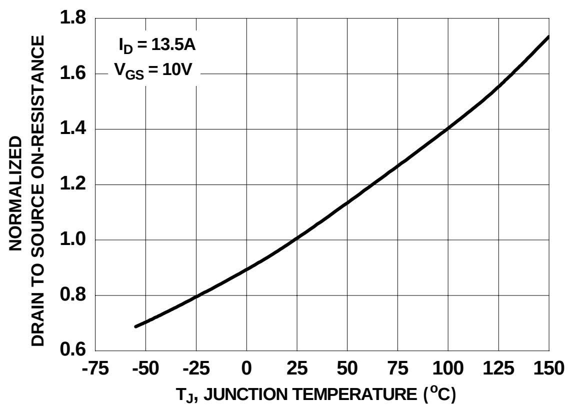


Figure 3. Normalized On-Resistance vs Junction Temperature

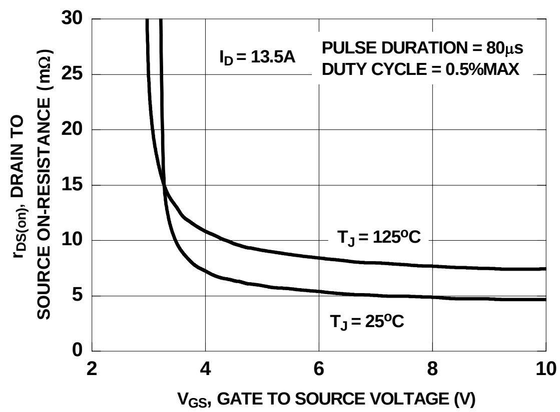


Figure 4. On-Resistance vs Gate to Source Voltage

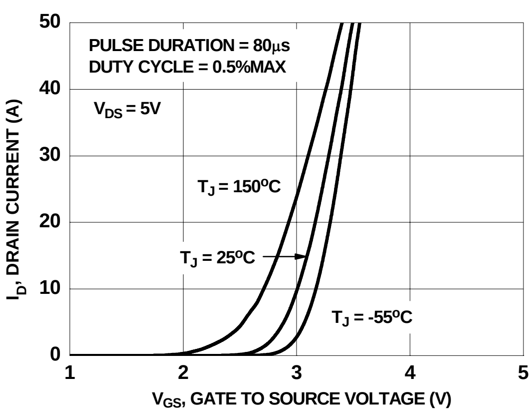


Figure 5. Transfer Characteristics

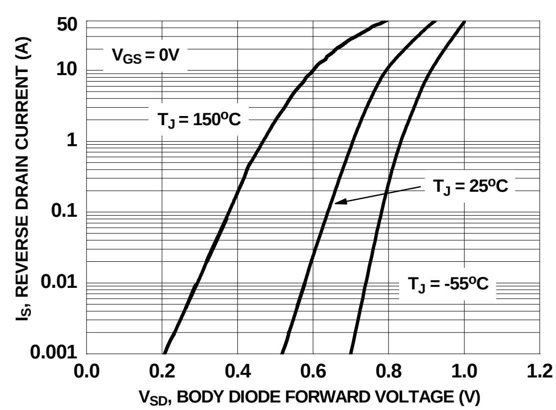


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

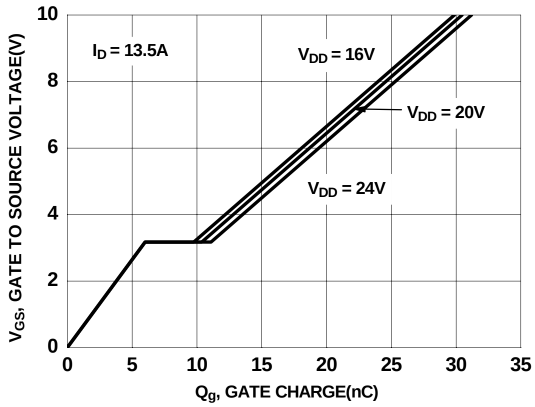


Figure 7. Gate Charge Characteristics

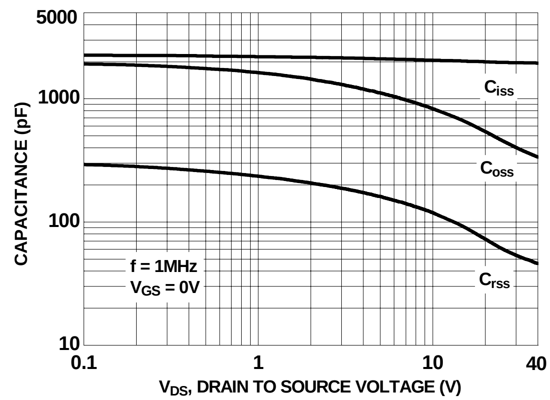


Figure 8. Capacitance vs Drain to Source Voltage

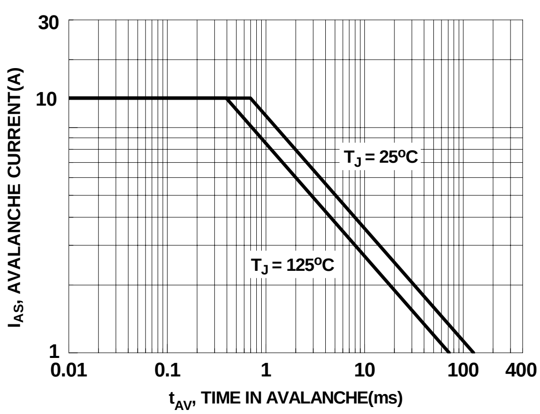


Figure 9. Unclamped Inductive Switching Capability

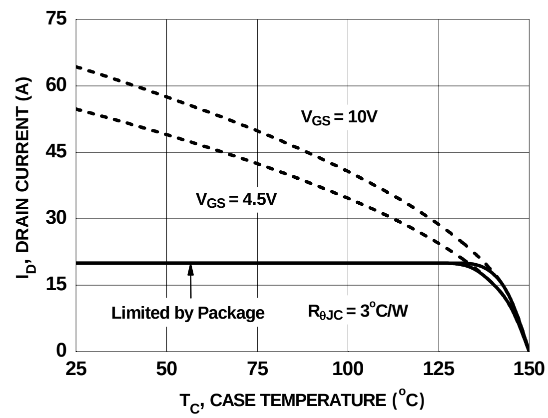


Figure 10. Maximum Continuous Drain Current vs Case Temperature

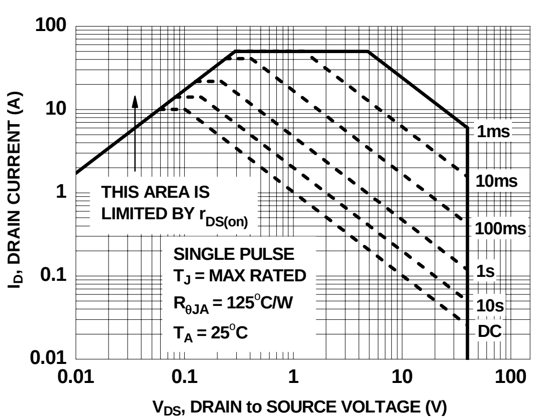


Figure 11. Forward Bias Safe Operating Area

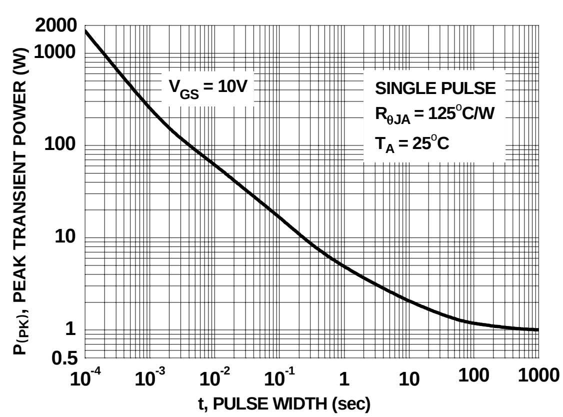


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25°C$ unless otherwise noted

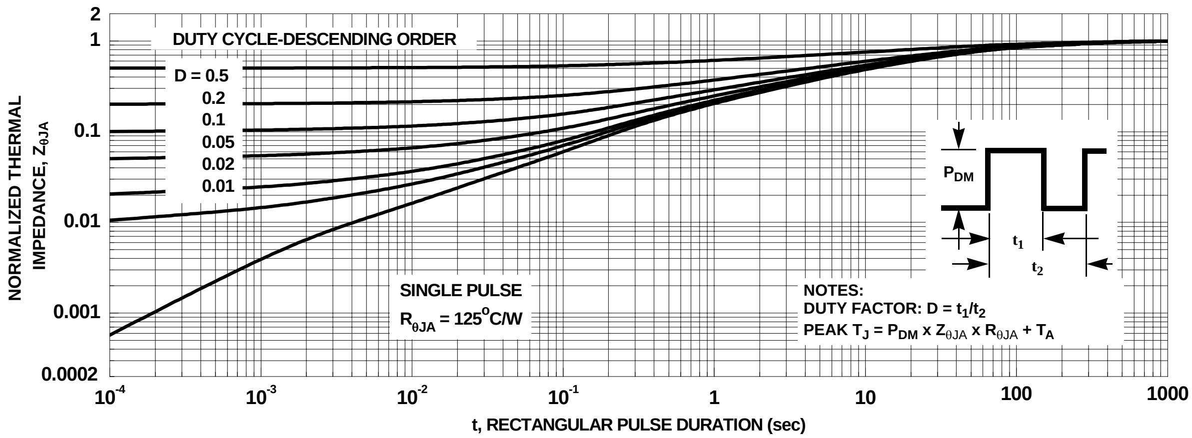
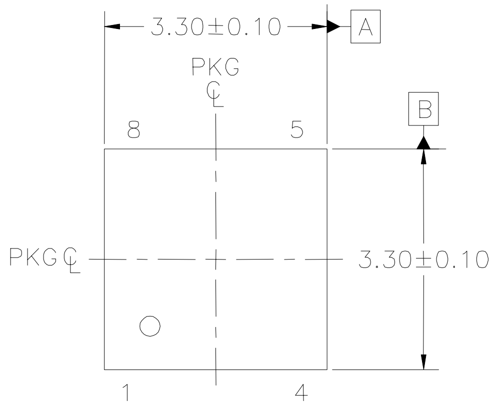
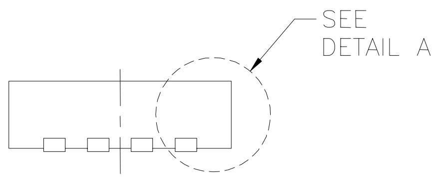
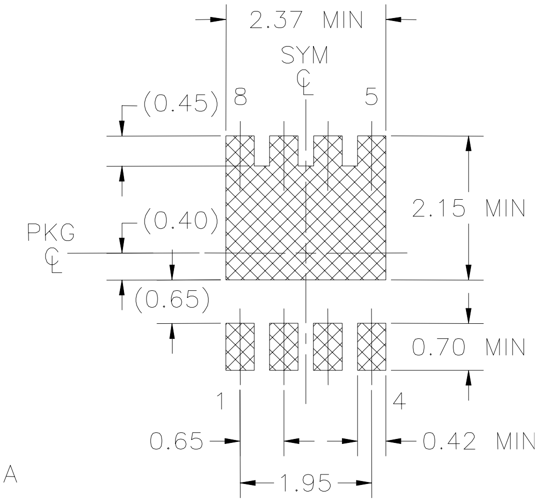


Figure 13. Transient Thermal Response Curve

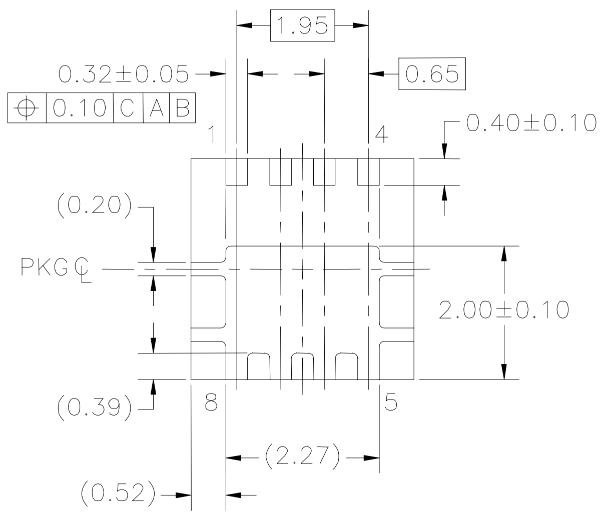
Dimensional Outline and Pad Layout

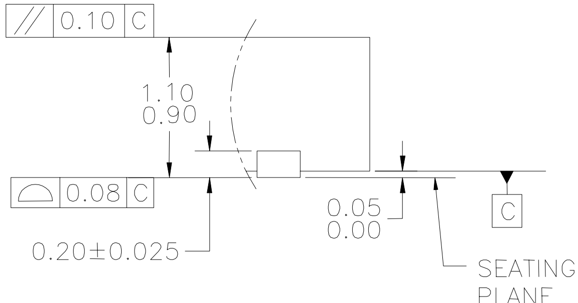






LAND PATTERN RECOMMENDATION





DETAIL A
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